

PHENIX FEE REVIEW BNL - 11/21/96

TGLDx Thin Glenn-Lund w/Discriminators for InterpolatingPad Chambers

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detector specifications

<u>PC2</u>

16pF

PC3

20pF

PC1

	detector capacitance:	5pF
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charge sensitivity/MIP: 18fC 29fC 36fC

min. charge of interest: 0.9fC 1.45fC 1.8fC

max channel rate: 200 counts/second





tgld function

- charge sensitive preamp with programmable reset, decay & channel disable
- passive CR differentiation
- leading edge discriminator with programmable threshold
- On chip charge calibration
- 16 channels per chip
- 1 milliwatt per channel





tgld preamp specifications pc1 pc2 pc3

charge gain t	to input o	of differentiator	(mV/fC):	20	12.4	10
criar Sc Sarri	io ilipat i	or annormator	$(111 \vee / 1 \bigcirc)$.	\sim 0	1~.1	10

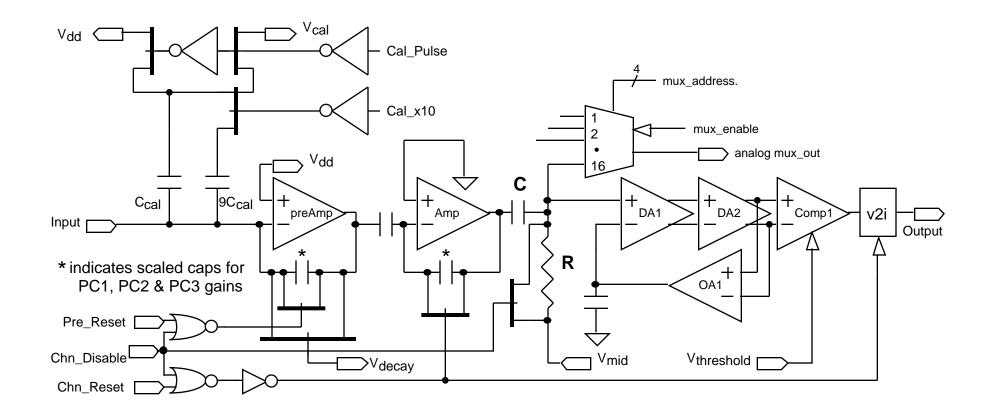
• rail output in MIPs:
$$>7 > 7 > 7$$

- feedback shorting reset switches
- onboard charge calibrator: 1-16fC(1fC steps), 10-160(10fC steps)
- nominal 100 nsec. **CR** passive output differentiator
- 200 μW per channel
- 16 channels per chip





tgld typical channel







tgld discriminator specifications

leading edge discriminator

programmable threshold: 10 - 320 mV (6-bit DAC)

maximum input offset: ±5mV

maximum delay time: 70 nsec

maximum reset time: 150 nsec (actual reset time is

dependent on input tail)

current output(nominal):
 100 μA asserted, 0 μA un asserted

800µW per channel

programmable channel disable

• 16 channels per chip





manufacturing plan

- Orbit or H-P 1.2 μm CMOS process with linear caps
- design new tgld after major requirements revision 9/96 (Dec 96)
- protype thru Orbit Foresight or MOSIS brokerage and test revised design (parts out Mar 97)
- tweak new design based on evaluation units (Apr 97)
- fab short lot of preproduction wafers and test for "known good die" with MOSIS' IMS tester and special ORNL supplied test boards and vectors (Jul 97)
- develop Iqq test vectors and reject/accept criteria (Aug 97)
- fab production wafer run thru Orbit or H-P and wafer test with Iqq requirements (Nov 97)





preamp/disc. test plans

- Acquire dedicated probe card for tgldx to fit MOSIS test station
- develop any special hardware to test analog portions in conjunction with IMS digital tester at MOSIS
- evaluate 1st silicon of revised tgldx at die level at MOSIS and on ROC at Lund
- attempt Iqq testing on short wafer run of tgldx at MOSIS
- determine if Iqq testing is feasible for analog screening for Known Good Die
- develop special HW & SW for production testing of ROC
- test production run of tgldx at MOSIS with Iqq or special HW





development status

TGLDx chips

- three designs; one each for PC1, PC2 & PC3
- design complete in Dec 1996
- Prototype run for TGLD1, TGLD2 & TGLD3 in Dec 1996
- single fab run with shared retical

readout card

layout new ROC based on TGLDx pinout Nov 1996

